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Commissioner of Patents and Trademarks Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572 20 McIntosh Drive Poughkeepsie, N.Y. 12603

Subject:

Serial No. 09/442,499 11/18/99

Paul Kwok Keung Ho, Xue Chun Dai

PLASMA ETCH METHOD FOR FORMING PLASMA ETCHED SILICON LAYER

| Grp. Art Unit: 1765

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

U.S. Patent 5,456,796 to Gupta et al., "Control of Particle Generation within a Reaction Chamber", discloses plasma processing method for attenuating particulate generation and deposition upon a substrate employed within a microelectronic fabrication when processing the substrate employed within the microelectronic fabrication while employing the plasma processing method.

CS-99-065

- U.S. Patent 5,681,424 to Saito et al., "Plasma Processing Method", discloses a plasma etch method using HBr.
- U.S. Patent 5,705,080 to Leung et al., "Plasma-Inert Cover and Plasma Cleaning Process", discloses a plasma cleaning process.
- U.S. Patent 5,811,356 to Murugesh et al., "Reduction in Mobile Ion and Metal Contamination by Varying Season Time and Bias RF Power during Chamber Cleaning", teaches a season time variation during chamber clean.
- U.S. Patent 5,824,375 to Gupta, "Decontamination of a Plasma Reactor using a Plasma after a Chamber Clean", discloses a plasma processing method and a plasma processing apparatus for reducing fluorine and other sorbable contaminants in a plasma reactor chamber employed within a chemical vapor deposition (CVD) method, such as but not limited to a plasma enhanced chemical vapor deposition (PECVD) method.

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